October 22 (Thu.), 2026

[Oral 10] CMP Fundamentals

09:45-11:10

International Conference Hall (B1F)

● Session Chair: Xinchun Lu (Tsinghua Univ., China)

09:45-10:10 [Oral 10-1]	**[Invited]** Research on Atomic-scale Tribochemistry Underlying Wafer-Scale Global Planarization of Advanced Integrated Circuits Lifei Zhang, Xinchun Lu (Tsinghua Univ., China), Knut Christoph Gottfried, and Jinji Luo-Hofmann (Fraunhofer Inst. for Electronic Nano Systems ENAS, Germany)
10:10-10:30 ★[Oral 10-2]	Clarification of Polishing Mechanism Focusing on Abrasive Particle Behavior in CMP - Relationship between Abrasive Particle Behavior and Pad Surface Topography in Micro Replicated CMP Pad - Haruto Kurokawa, Yoji Oyama, Syuhei Kurokawa, Terutake Hayashi, Keisuke Osawa (Kyushu Univ., Japan), Hirokuni Hiyama, Yutaka Wada, Naoyuki Handa, and Syuntaro Hayashi (Ebara Corp., Japan)
10:30-10:50 ★[Oral 10-3]	Micro-Structured Pads for High-MRR and Low-Damage Oxide Chemical Mechanical Polishing Seounghee Yun, Hyun Jun Ryu, Hyeongmin Je, and Sanha Kim (KAIST, Korea)
10:50-11:10 ★[Oral 10-4]	Physics-Informed Friction Coefficient Distribution Modeling for Material Removal Rate Prediction in Chemical Mechanical Polishing Sho Hirono (Kobe Univ., Japan), Chihiro Mitani (Chuo Univ., Japan), Takumi Sato, Kodai Hirano (Ebara Corp., Japan), and Norikazu Suzuki (Kobe Univ., Japan)